PTO/SB/08A(10-01)
Approved for use through 10/31/2002, OMB 651-0031
stem & Tredemerk Office; U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(Use as many sheets suggessary)

Application Numb r

Filing Date

First Named Inventor

Group Art Unit

2826

Examiner Name

Attorney Docket No: 1303.028US1

US PATENT DOCUMENTS									
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate			
76	US-6,461,931	10/08/2002	Eldridge, Jerome M.	438	398	08/29/2000			
Tb.	US-6,586,797	07/01/2003	Forbes, Leonard, et al.	257	325	08/30/2001			

FOREIGN PATENT DOCUMENTS									
Examiner initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Τ²			

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No	include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
ガ		SHI, Y., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", IEEE Electron Device Letters, 19(10), (1998),pp. 388-390	
Th		ZHANG, "Atomic Layer Deposition of High Dielectric Constant Nanolaminates", Journal of The Electrochemical Society, 148(4),(2001),F63-F66	

RECEIVED
FEB-2 2004
FEB-2 2004
TECHNOLOGY CENTER 2800

EXAMINER

DATE CONSIDERED

122/04